

SSD Characterization: From Energy Consumption's Perspective

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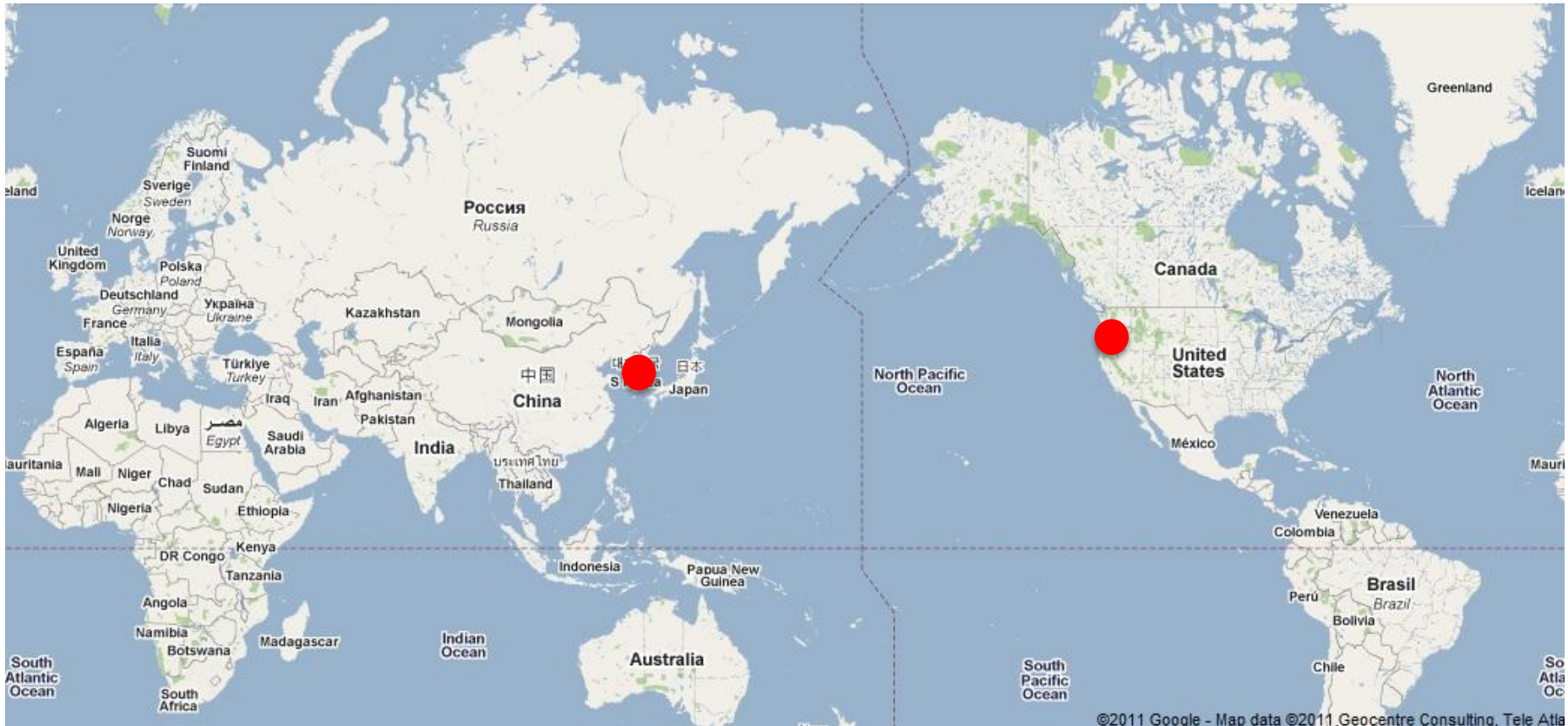
Dankook University



Sungroh Yoon

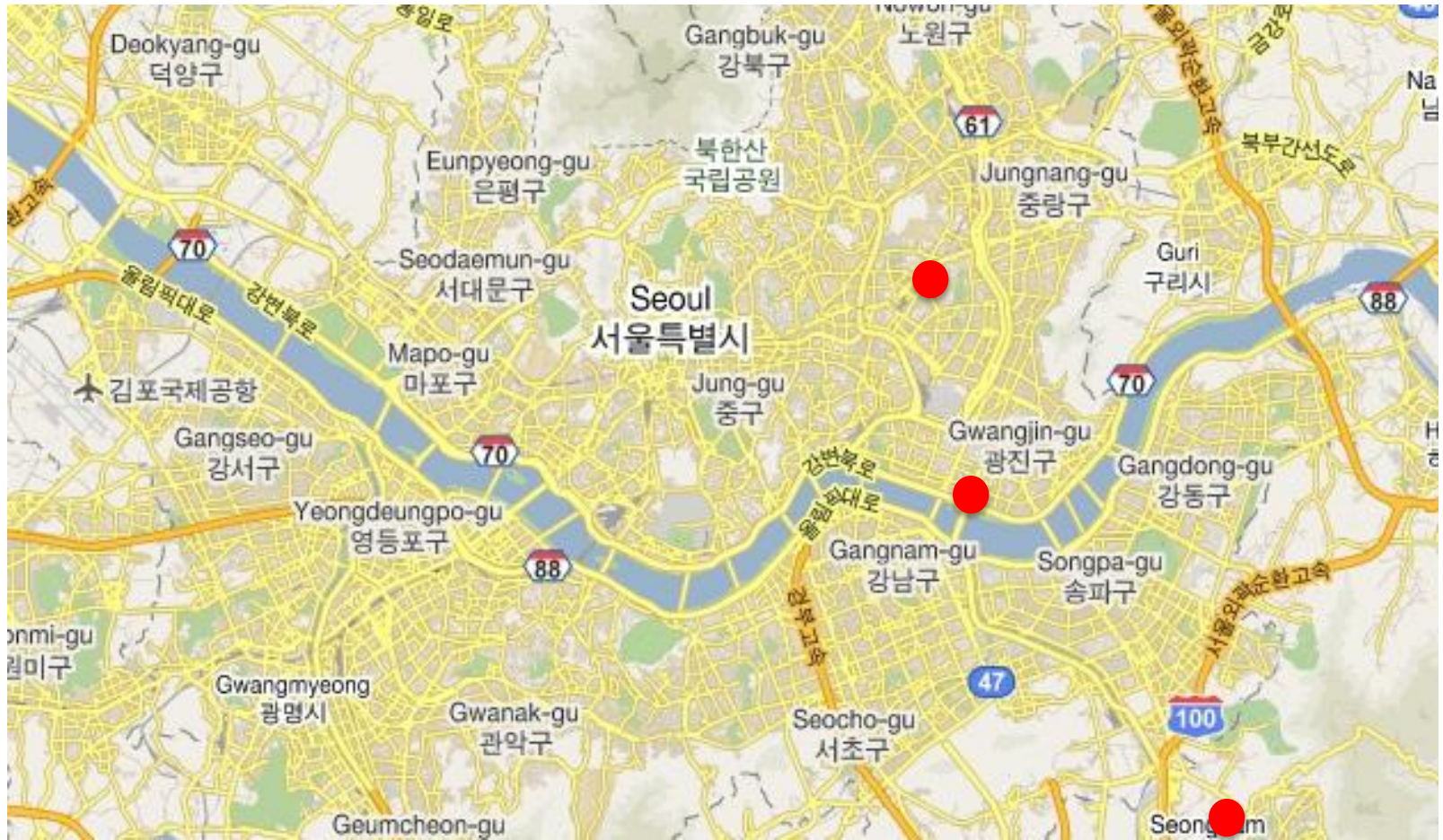
Korea University





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Outline

- Motivation
- SSD Organization and Energy Consumption
- Channels, Ways and Clusters
- Case Study
- Power Budget
- Conclusion

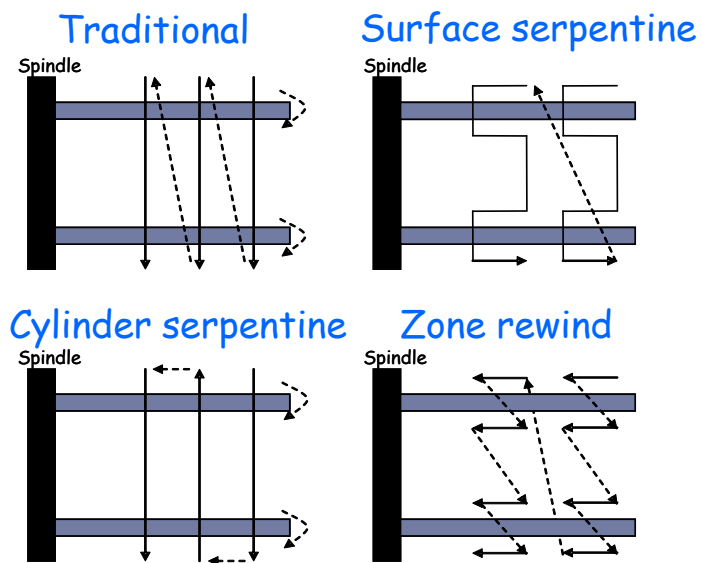
Motivation

Understanding of Internal Mechanism of Storage Device is very important!

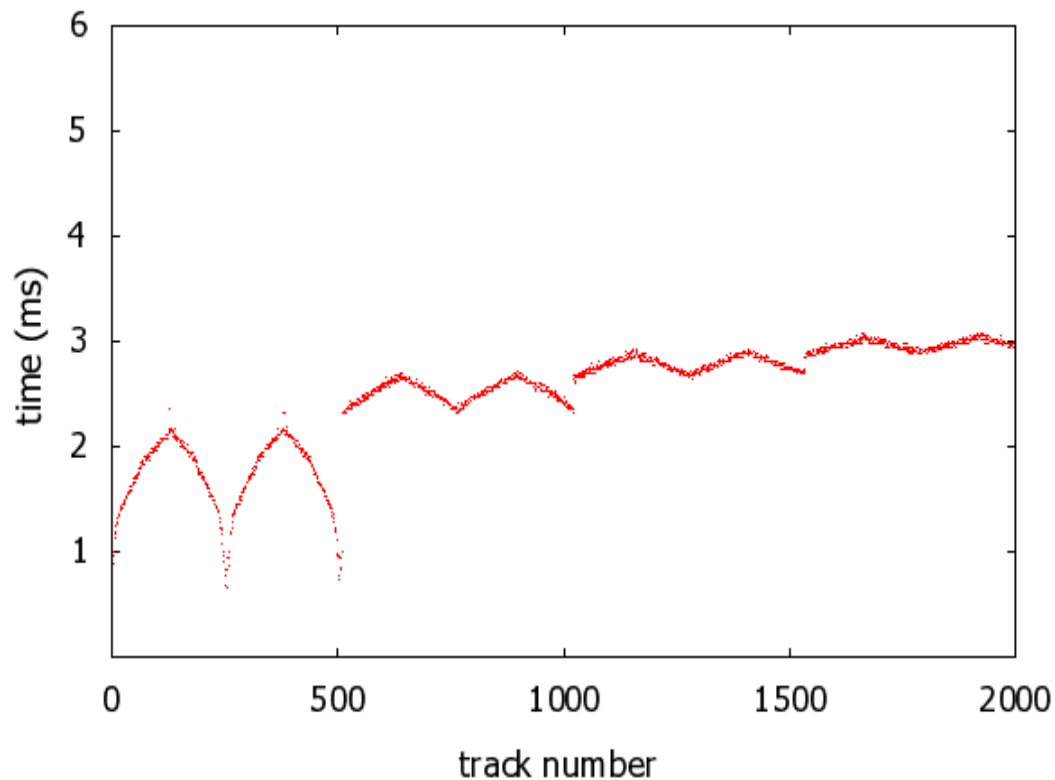
- Hard disk
 - ◆ Sector layout: cylinder serpentine vs. surface serpentine vs. hybrid serpentine
 - ◆ Number of zones
 - ◆ Degree of track skew
 - ◆ Disk scheduling algorithm

Characterizing HDD: Sector Layout

- Jongmin Gim et al, ACM ToS 6, 2 (July 2010)



Hitachi HDT7725032VLA360 for 2000 tracks



Characterizing Storage Devices

HDD Characterization is via measuring **Seek time** and **Rotational Latency**.

Characterizing SSD... what do we use?...

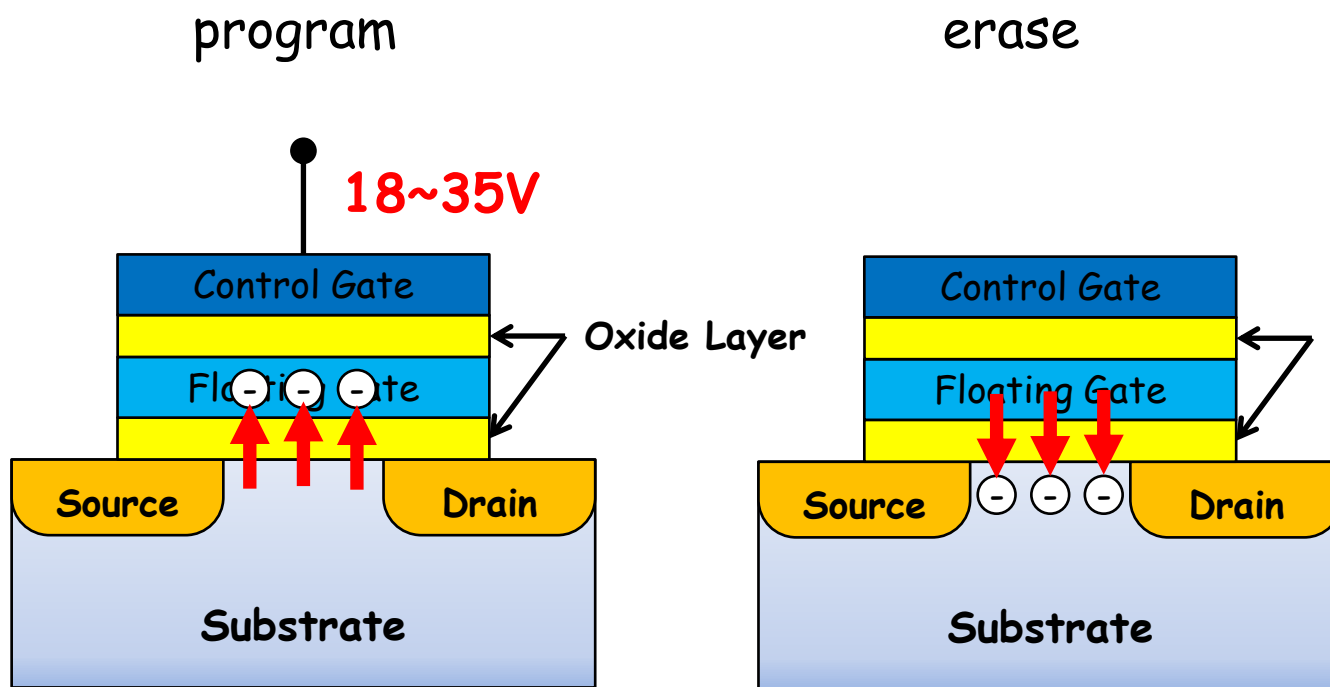


How do we figure out the internals of SSD?

- What is available
 - ◆ the number of channels
 - ◆ the number of chips/packages per channels

- What is not available?
 - ◆ Sector placement , Garbage collection algorithm

Operations on NAND Flash Cell



Operations on NAND Flash Cell



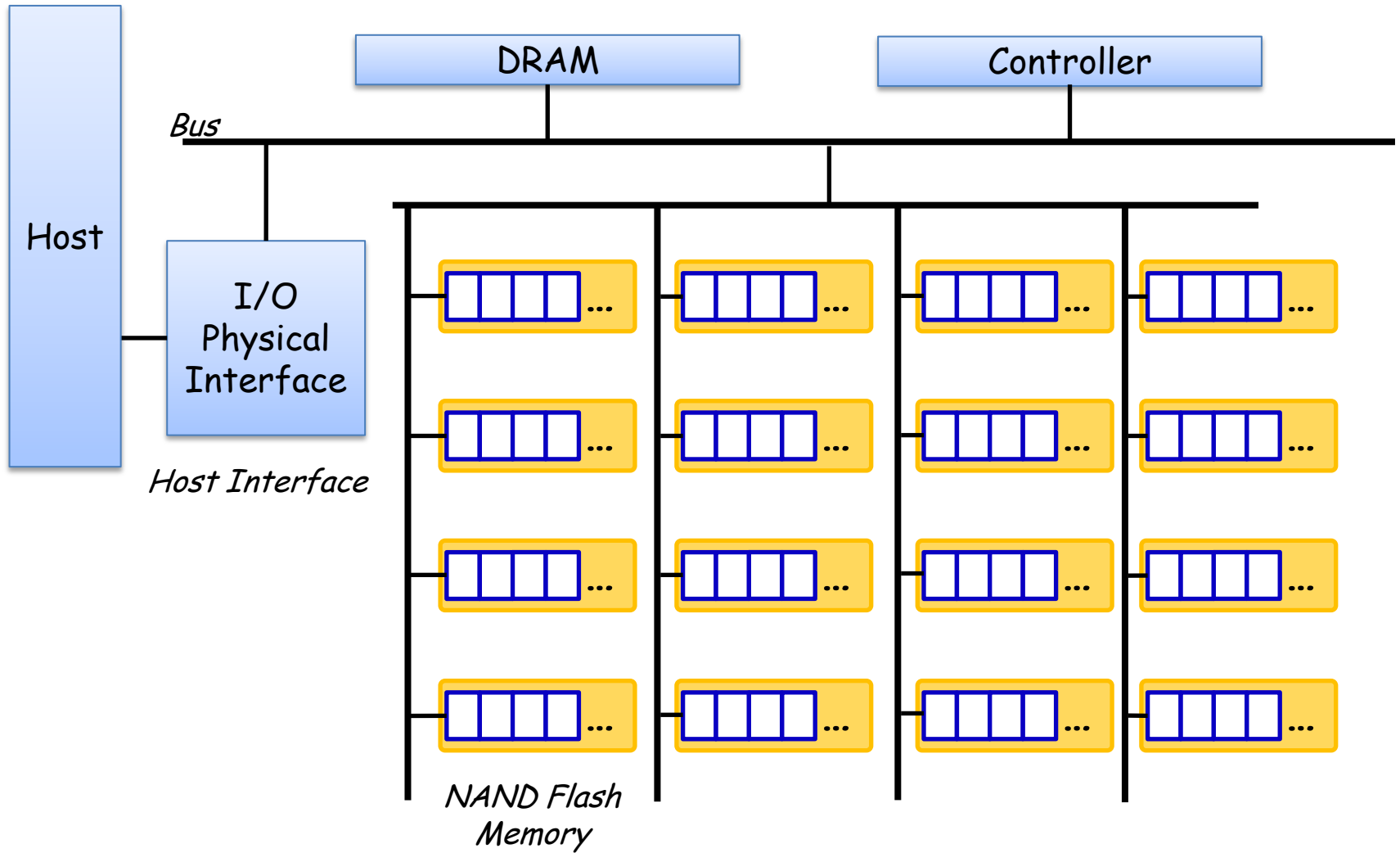
SSD Characterization

We will use "Energy Consumption"



SSD Organization and Energy Consumption

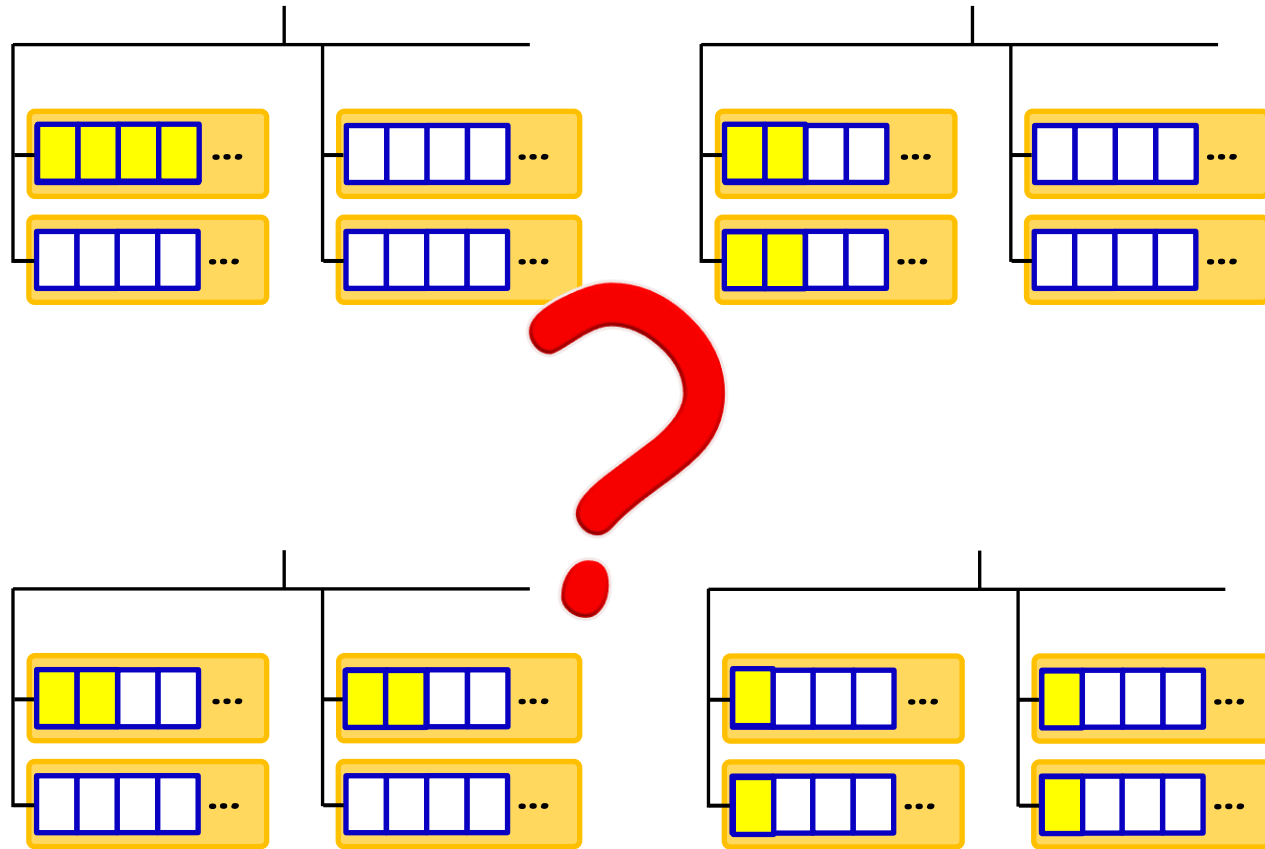
SSD Organization



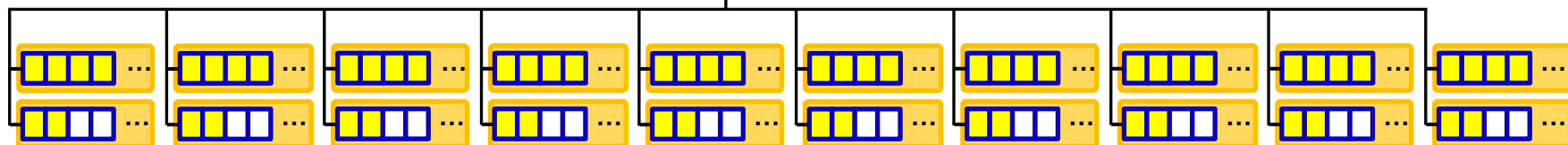
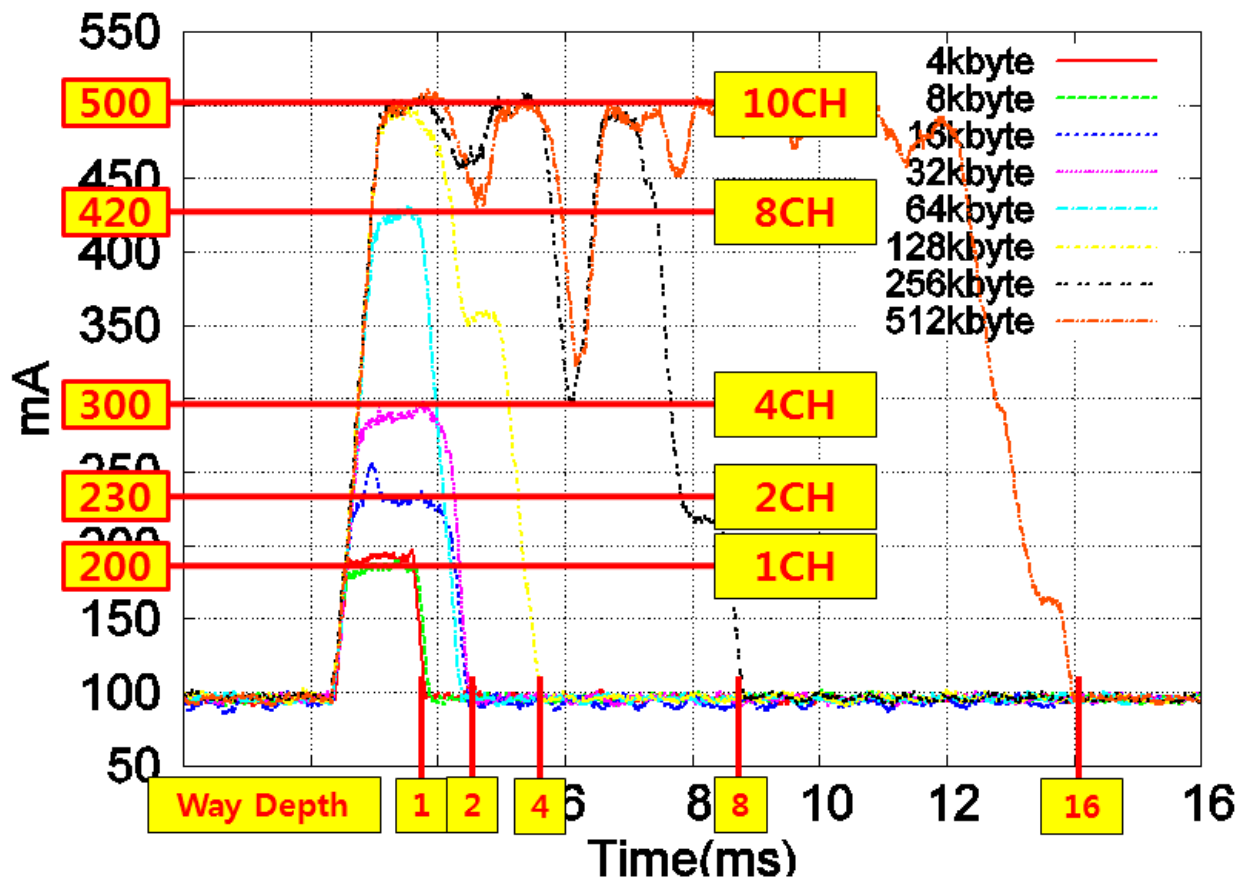
Characteristics of SSD Behavior

 =Page Write

 =Write Complete



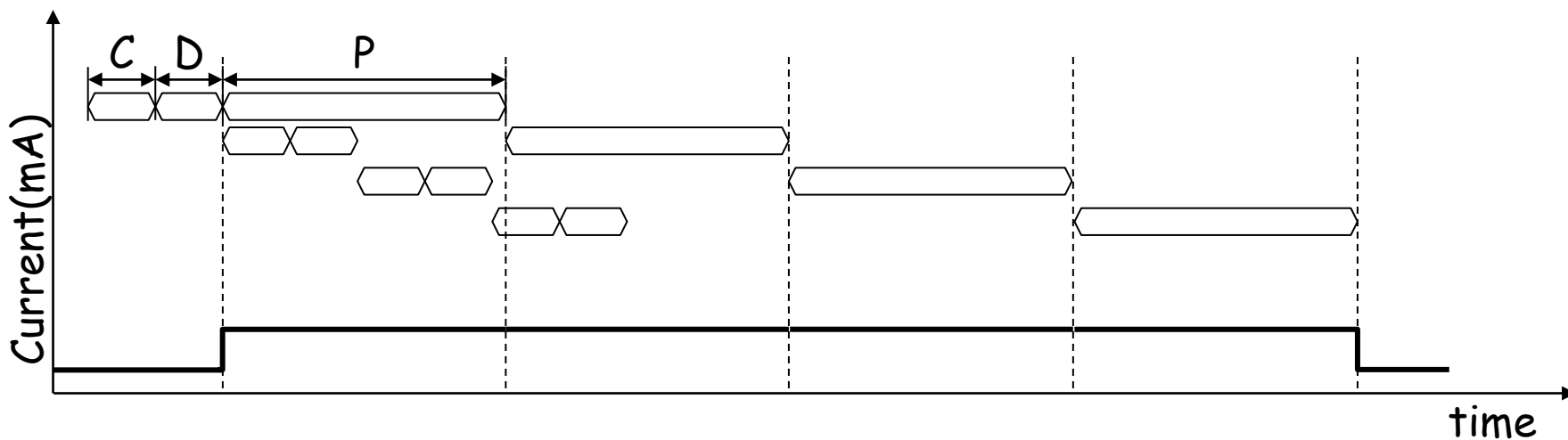
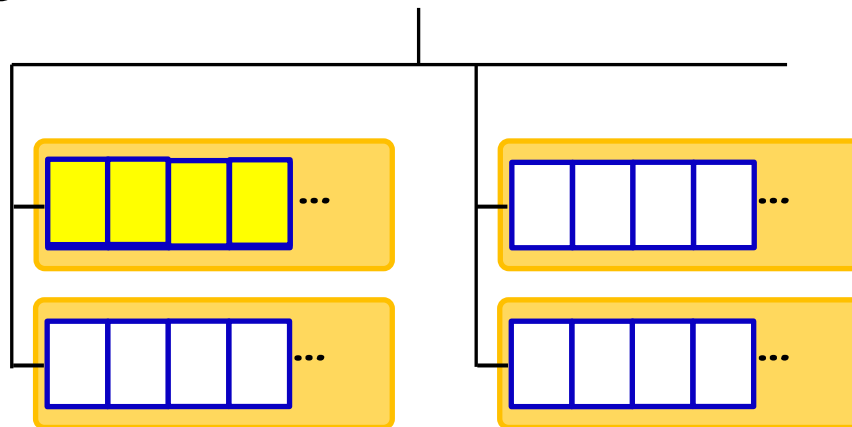
IO Size vs. Energy Consumption



Channels, Ways, and Clusters

Writing 4 pages: 1 Channel X 1 Way

- =Page Write
- =Write Complete

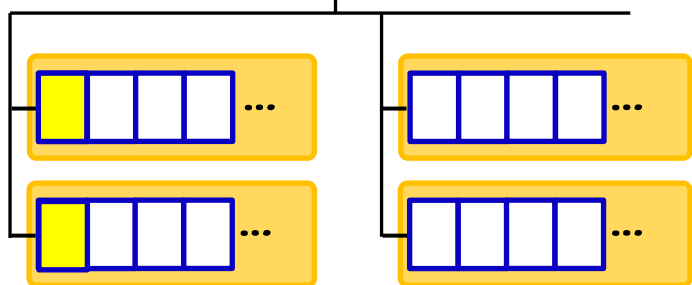


Way switch vs. Channel switch Delay

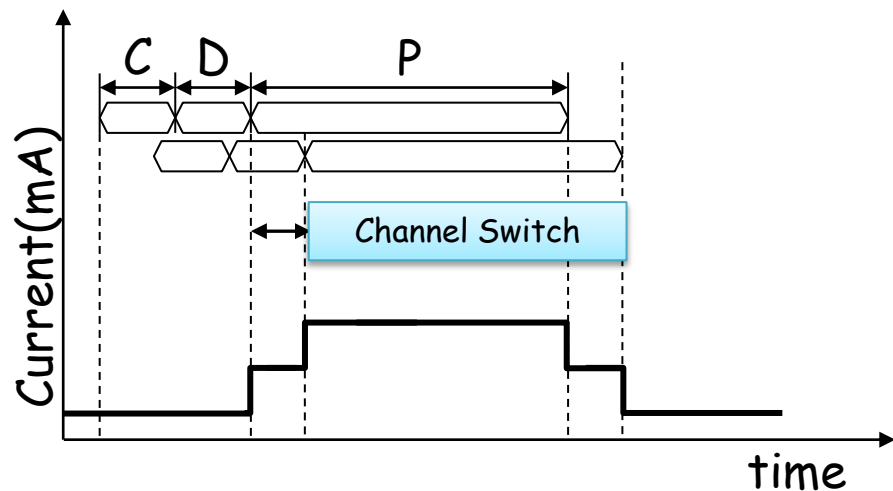
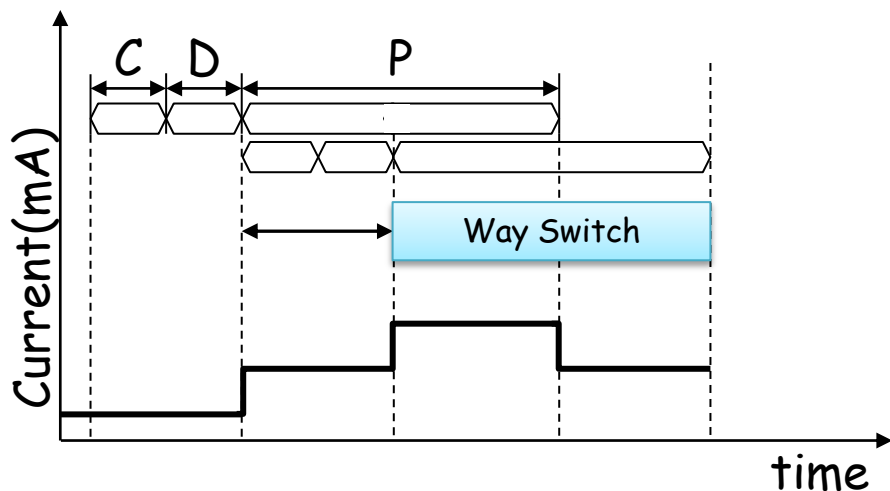
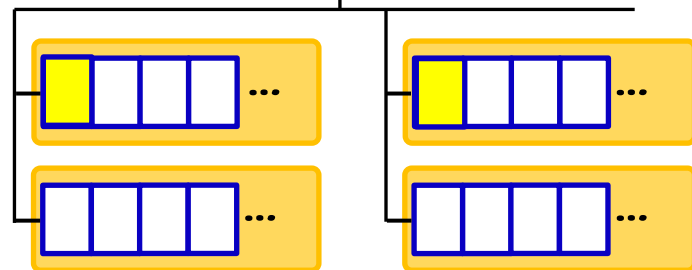
■ = Page Write

■ = Write Complete

Way Switch

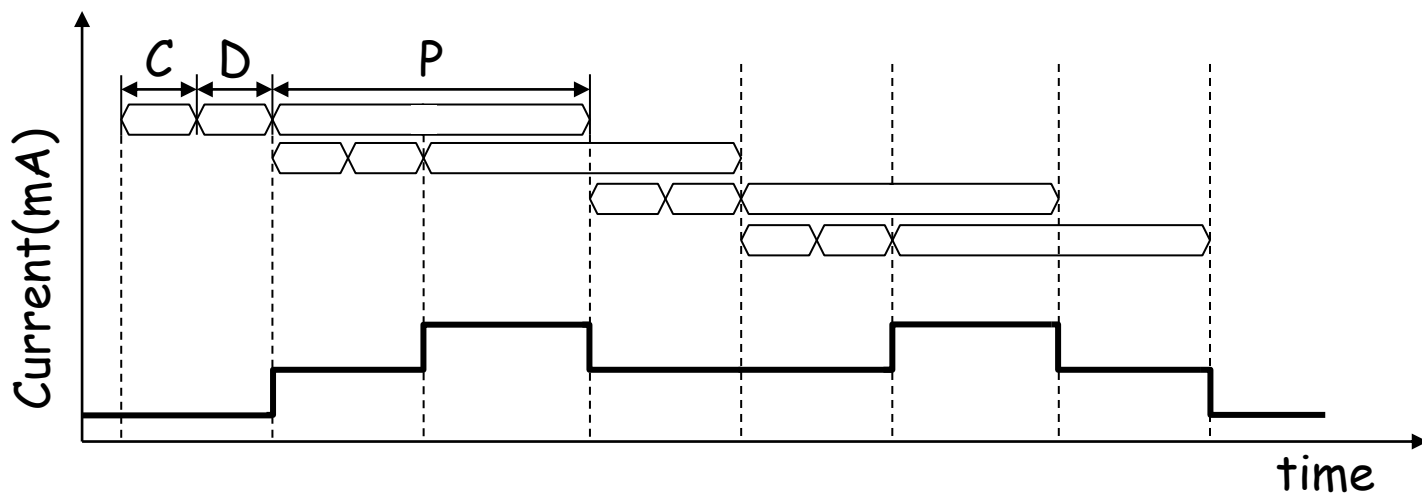
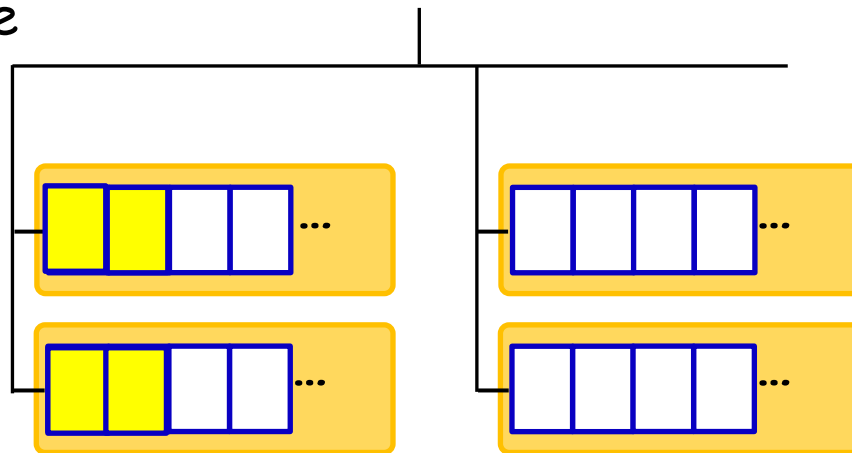


Channel Switch



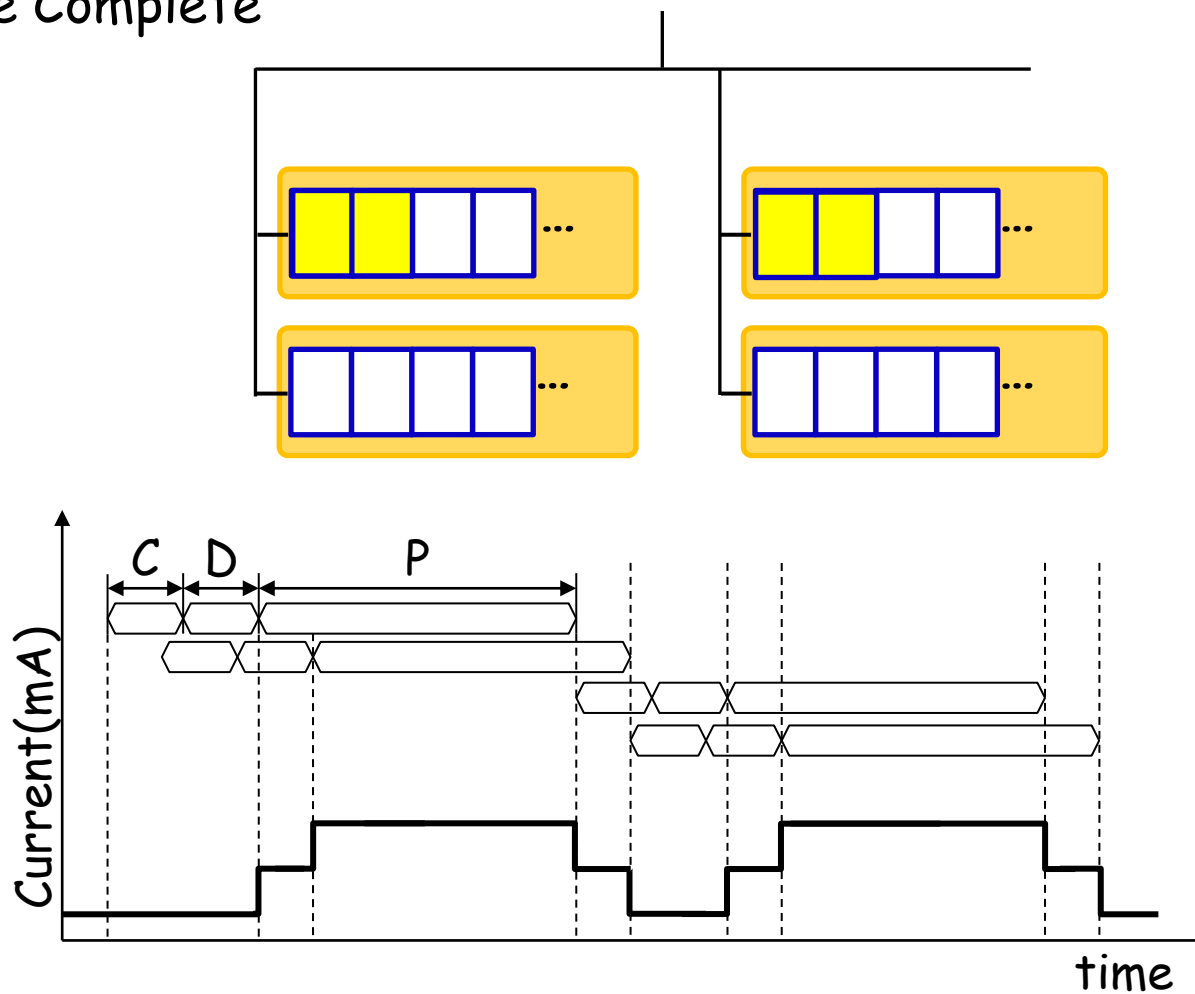
Writing 4 pages: 1 Channel X 2 Way

- =Page Write
- =Write Complete



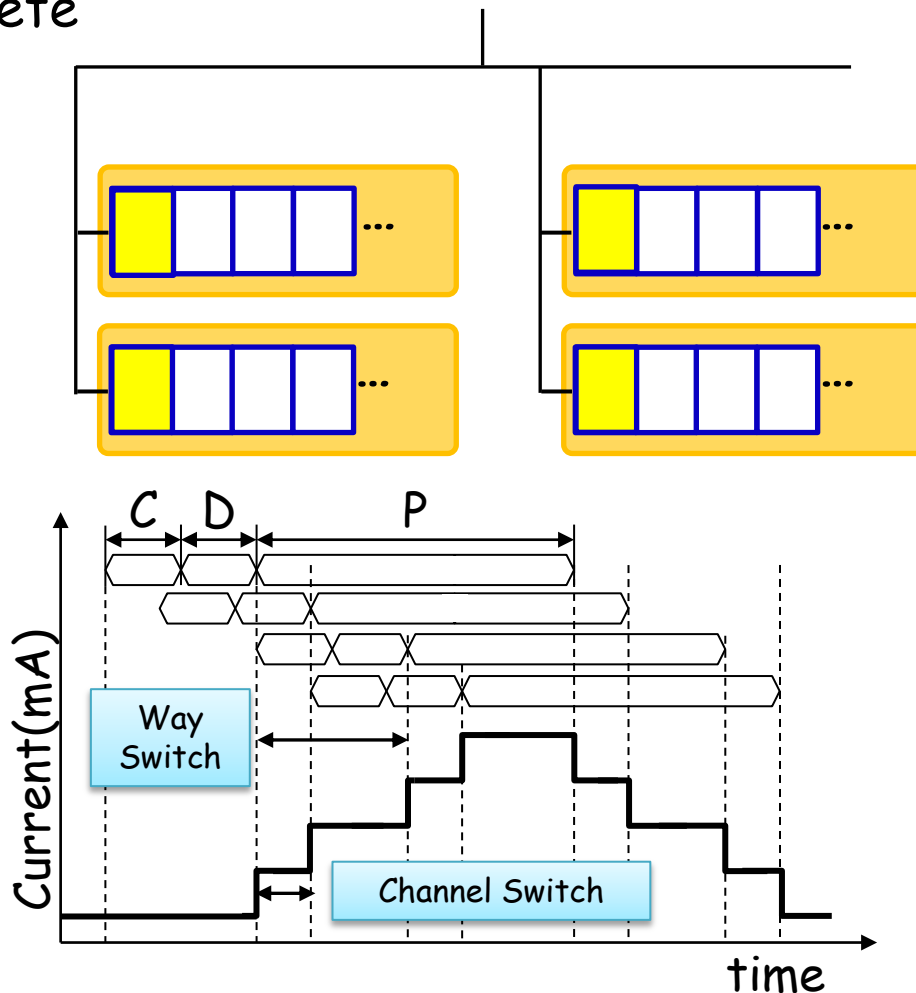
Writing 4 pages: 2 Channel X 1 Way

- =Page Write
- =Write Complete



Writing 4 pages: 2 Channel X 2 Way

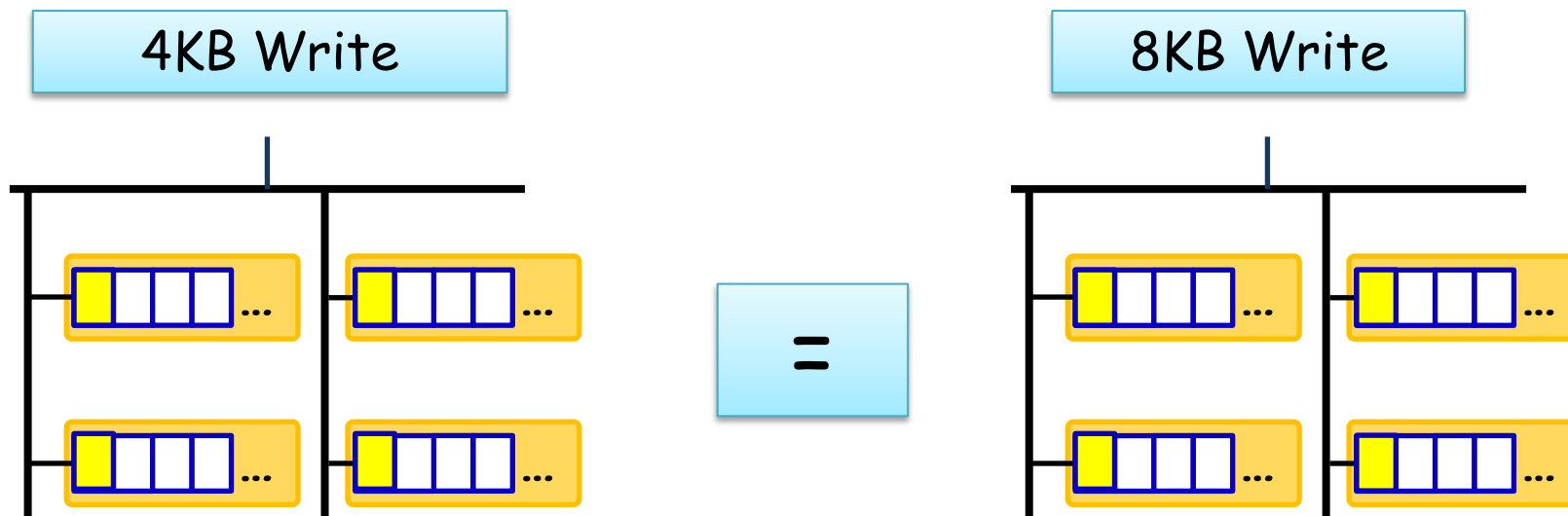
- =Page Write
- =Write Complete



Cluster

- Cluster : Write Unit of SSD

 =Page Write



Case Studies

Measurement

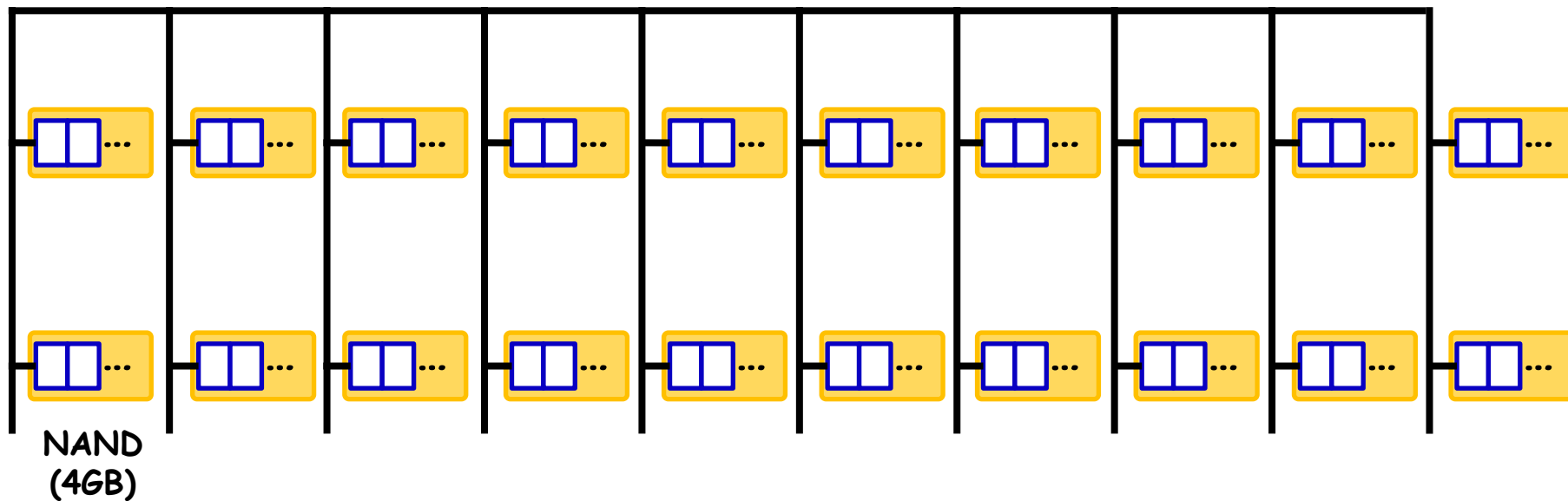
Model	Vendor	Size	Channels	DRAM Size	Package	Type
X25M	Intel	80GB	10	16MB	20	MLC
MXP	SAMSUNG	128GB	8	128MB	16	MLC

- Oscilloscope (TDS3032)
- High resolution current probe(TCP202)
- Current probe to power line(V_{dd}) of the SSD
- Sampling interval(10samples MA): 10 μ sec



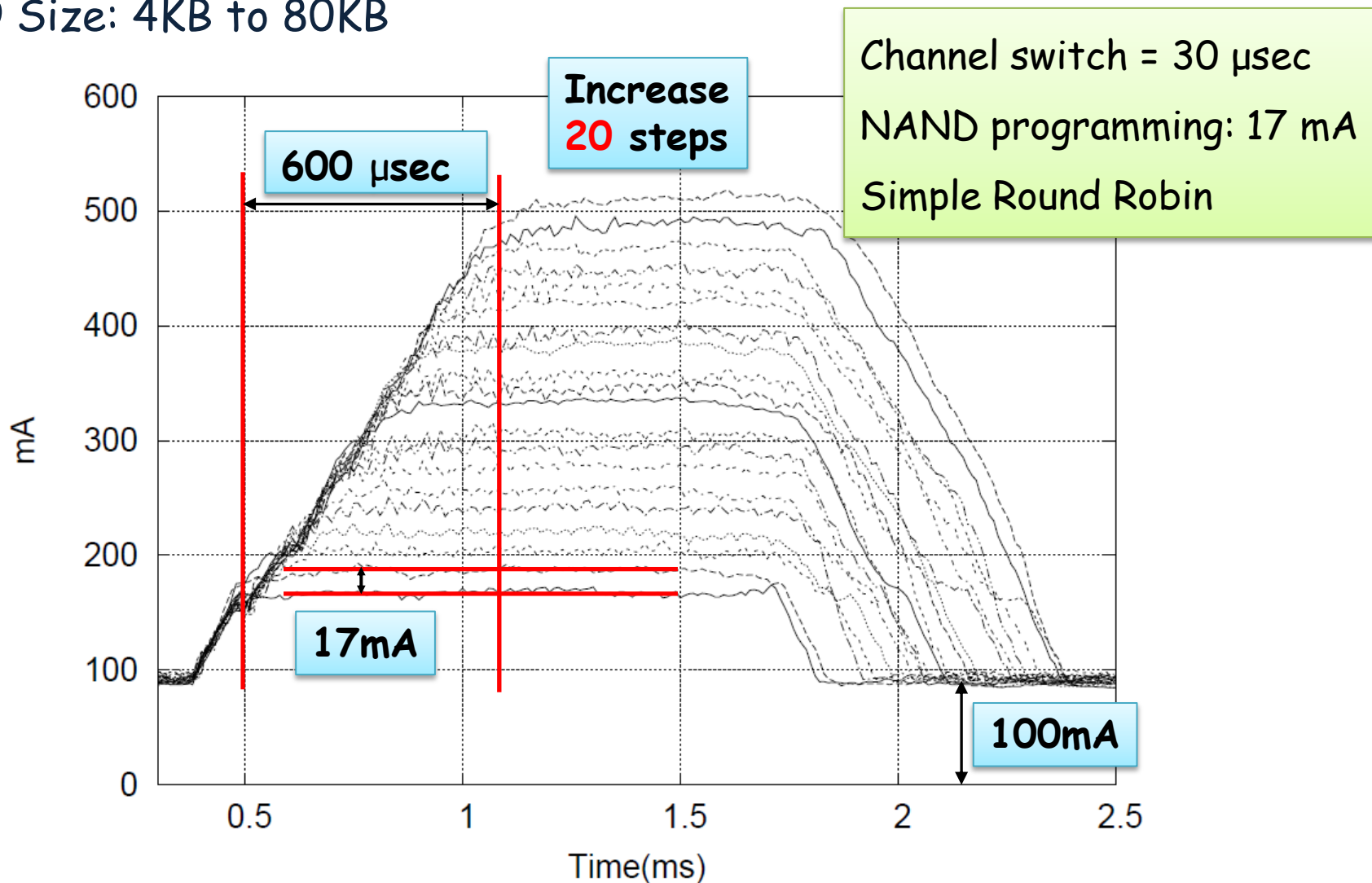
Case Study : Intel X25M

Capacity	80GB
No. of Channels	10
Packages/Channel	2
Package	4 GB



Case Study : Intel X25M

- IO Size: 4KB to 80KB

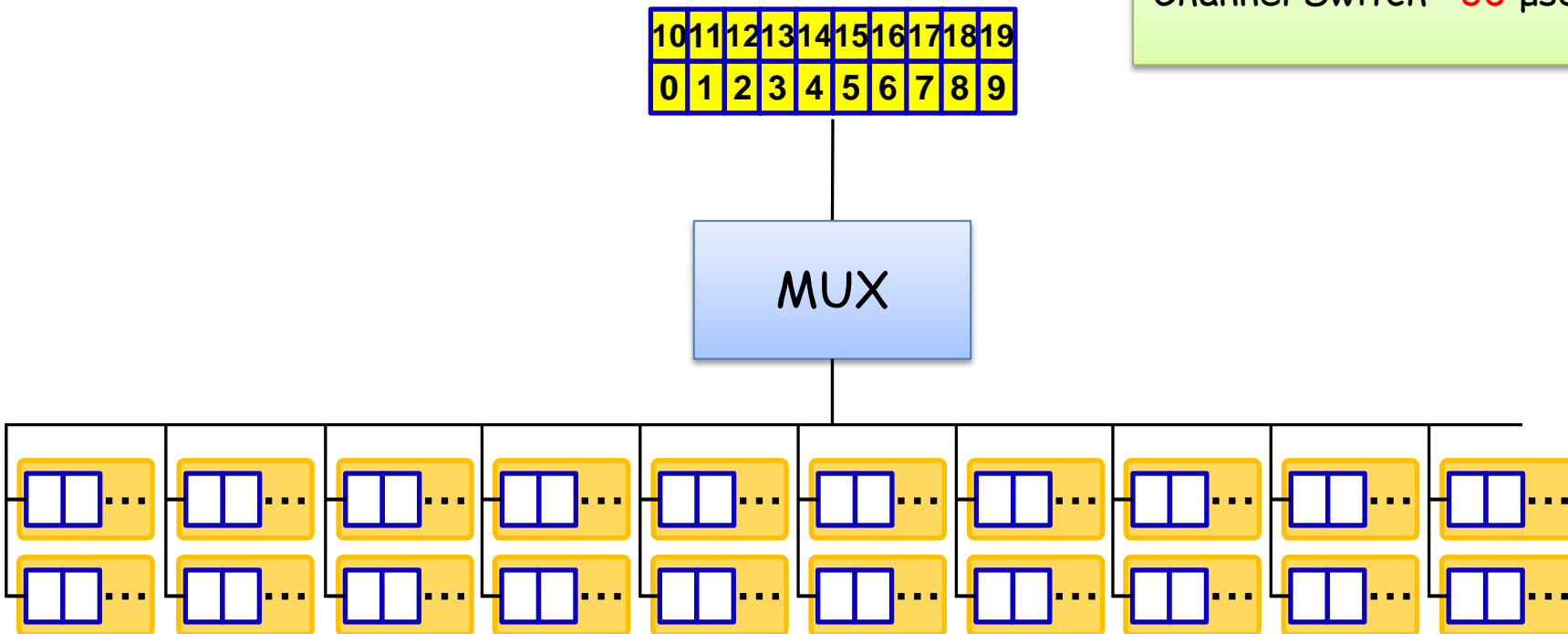


Case Study : Intel X25M

- 4KB to 80KB Sequential Write

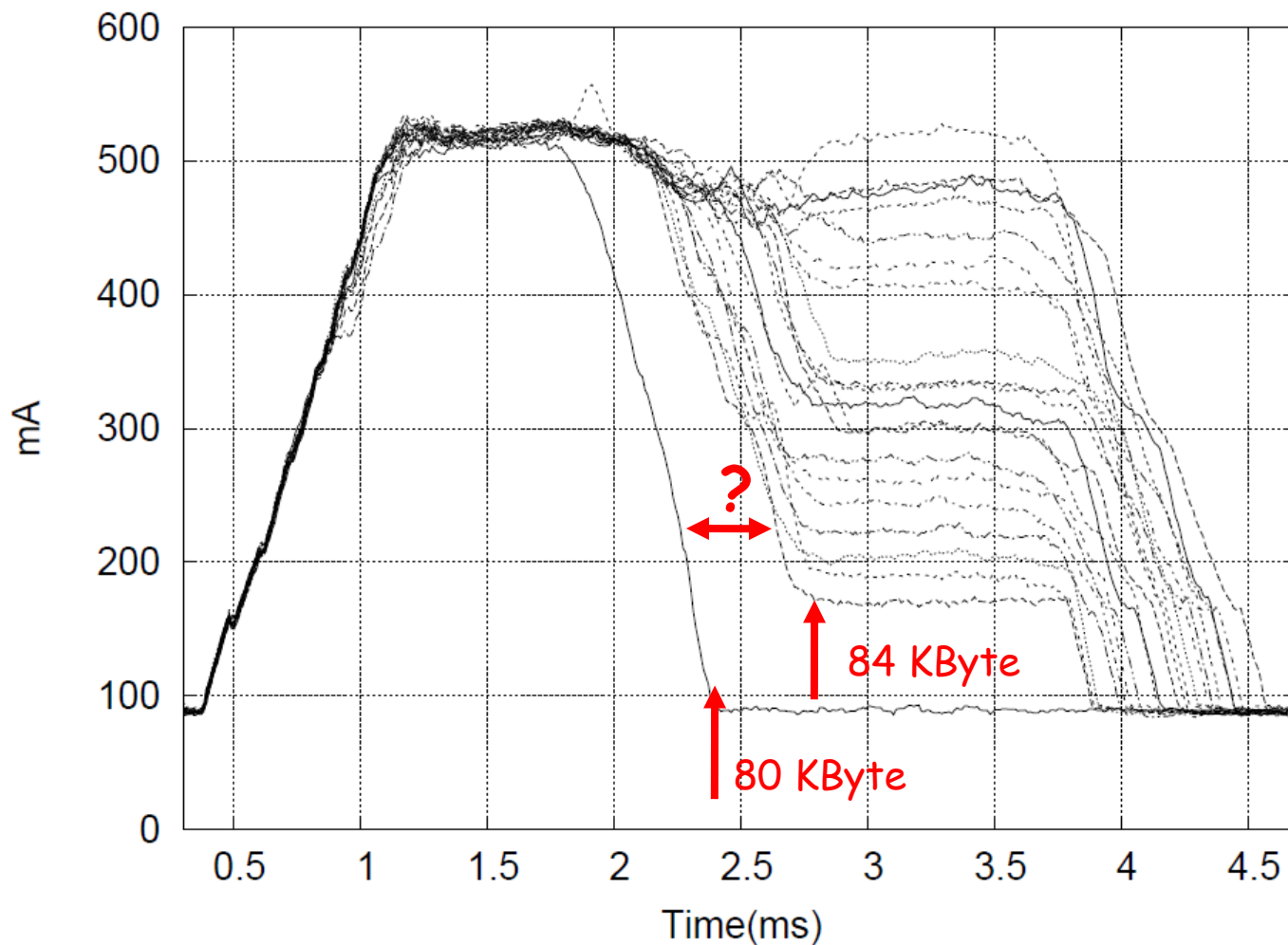
■ = Page Write

Channel Switch = 30 μ sec



Case Study : Intel X25M

80KB to 160KB Write



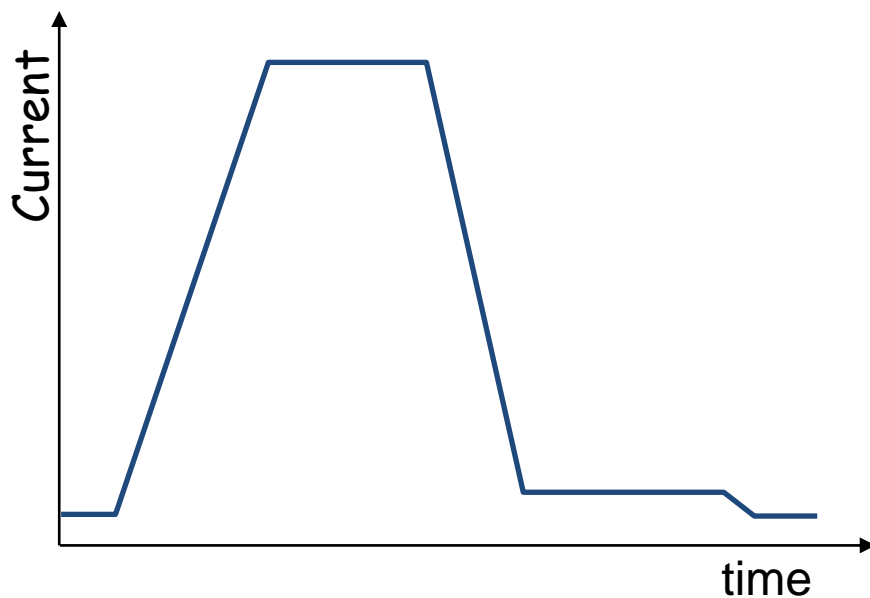
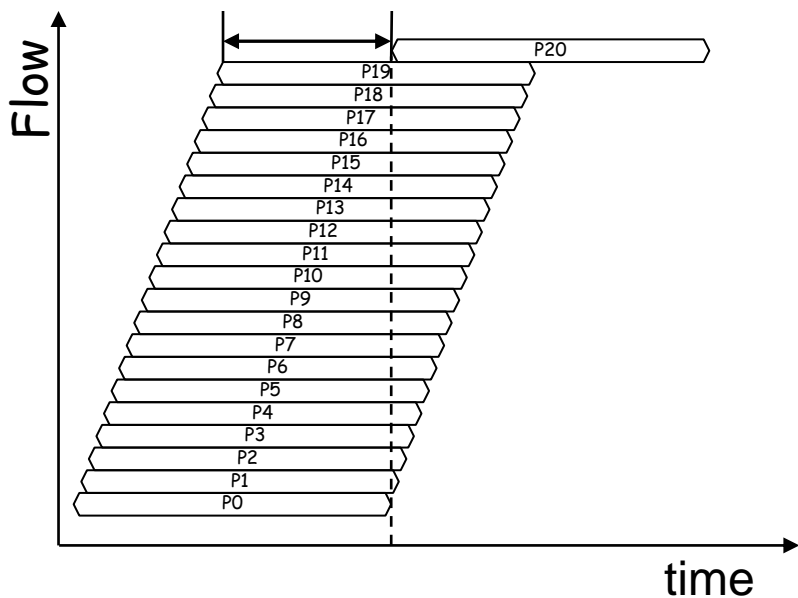
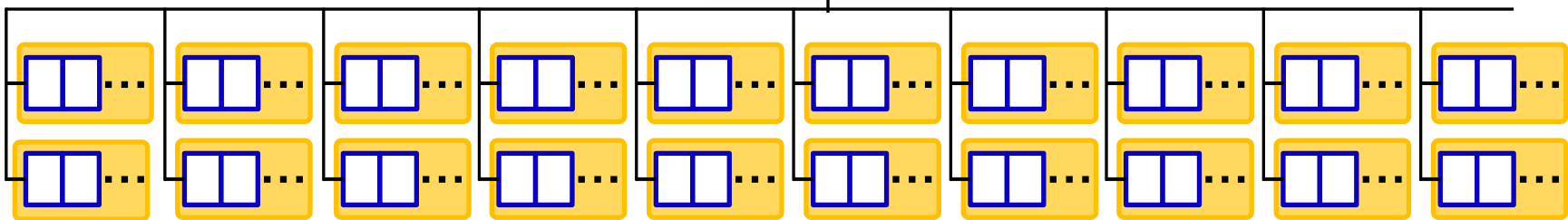
Case Study : Intel X25M

■ = 1 Page Write

■ = Write Complete

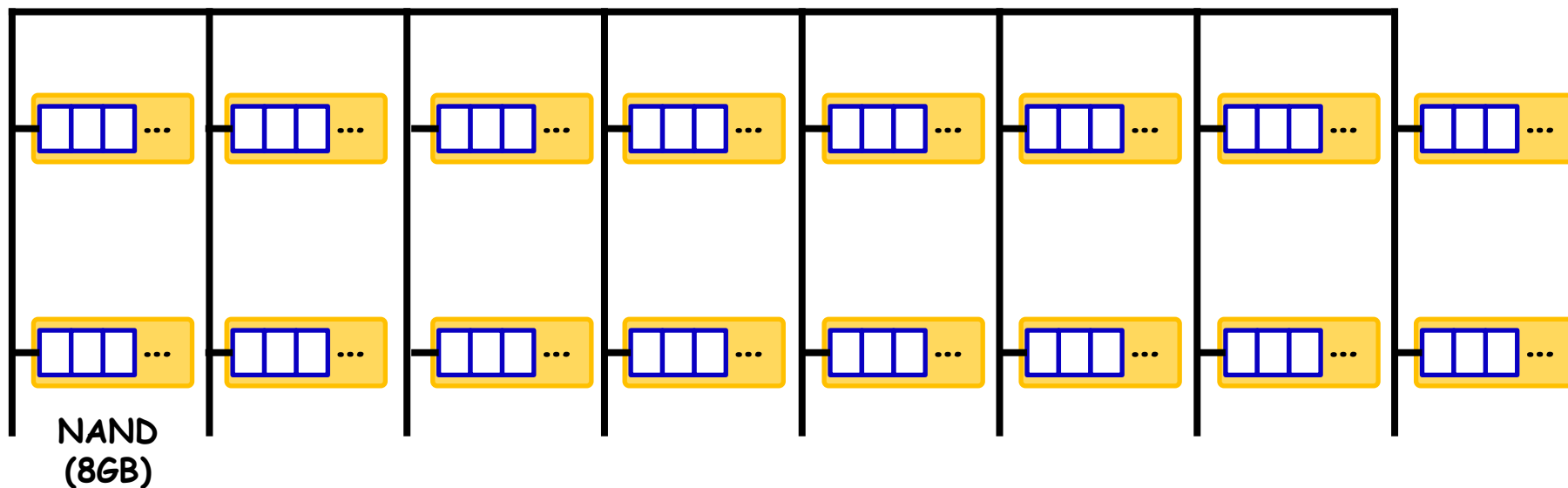
10	11	12	13	14	15	16	17	18	19
0	1	2	3	4	5	6	7	8	9

MUX

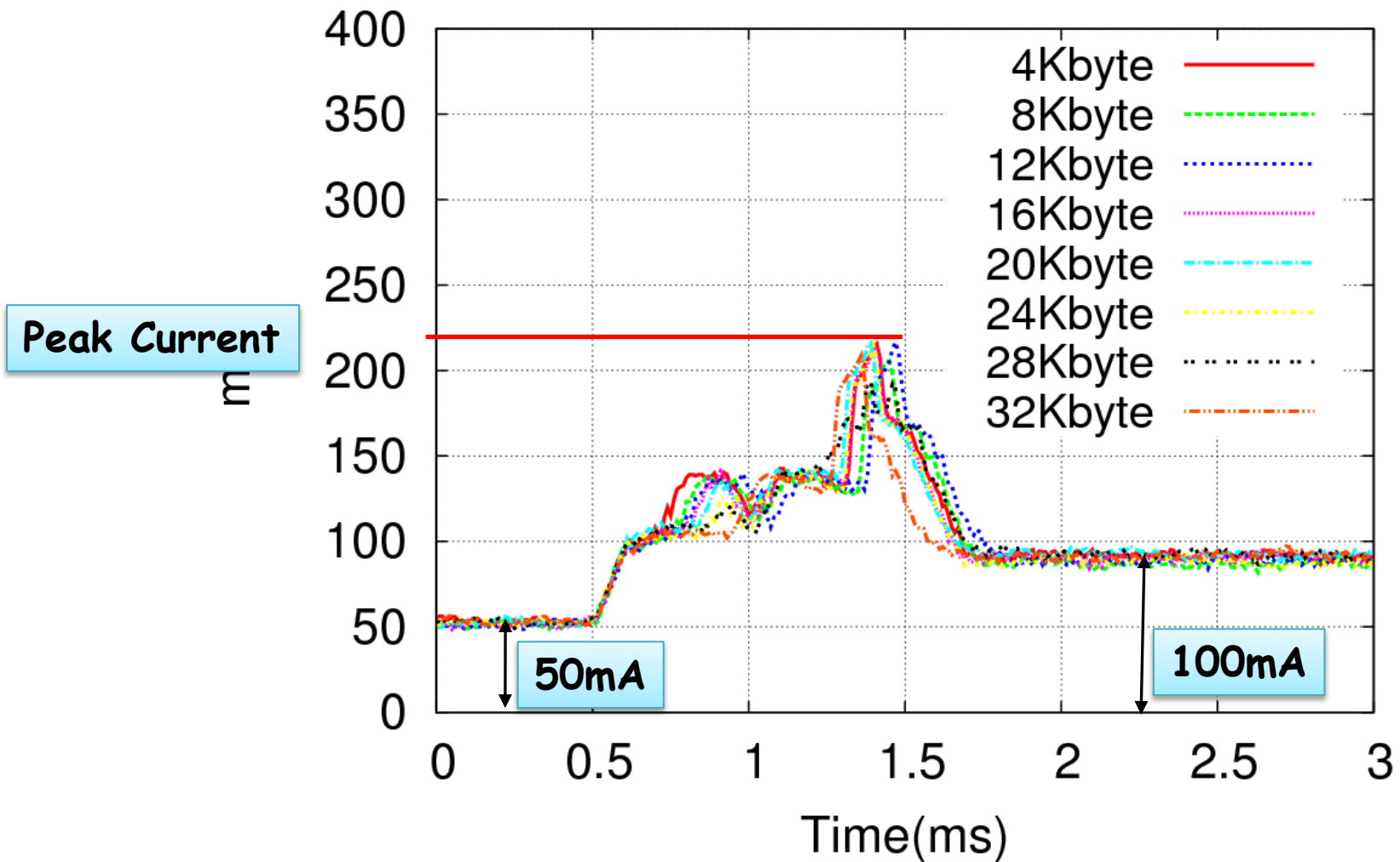


Case Study : SAMSUNG MXP

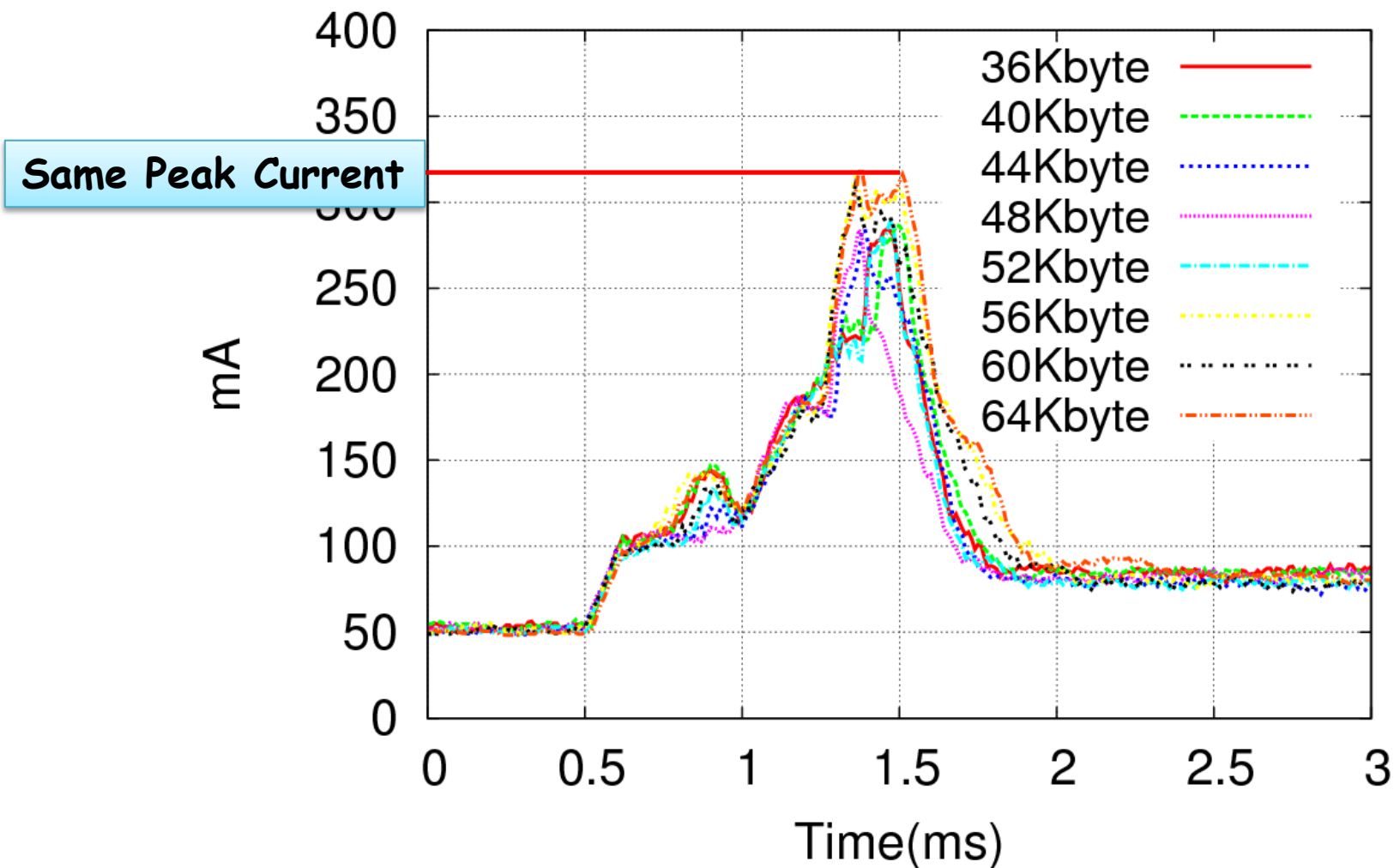
Capacity	128GB
No. of Channels	8
Packages/Channel	2
Package	8 GB



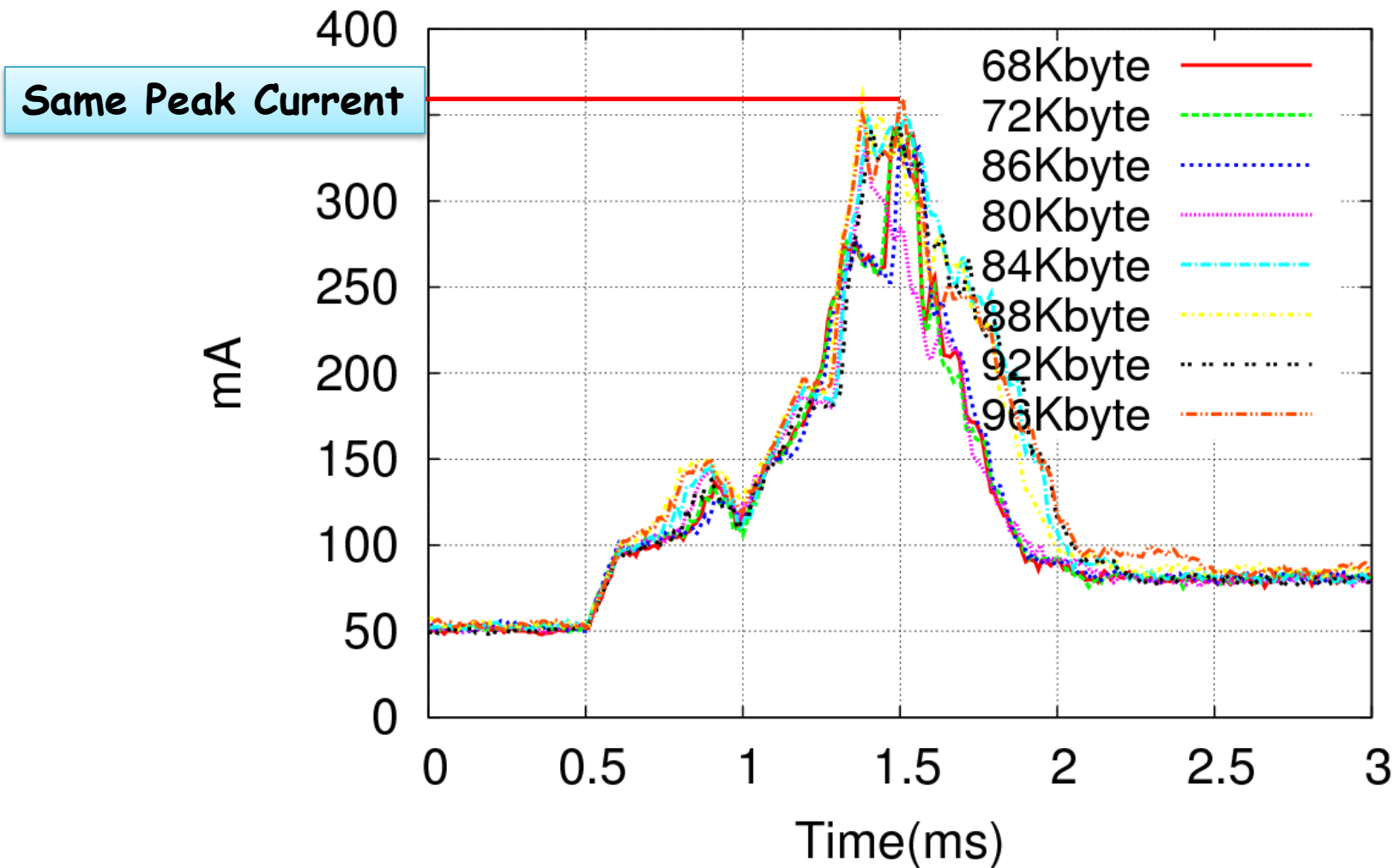
Case Study : SAMSUNG MXP



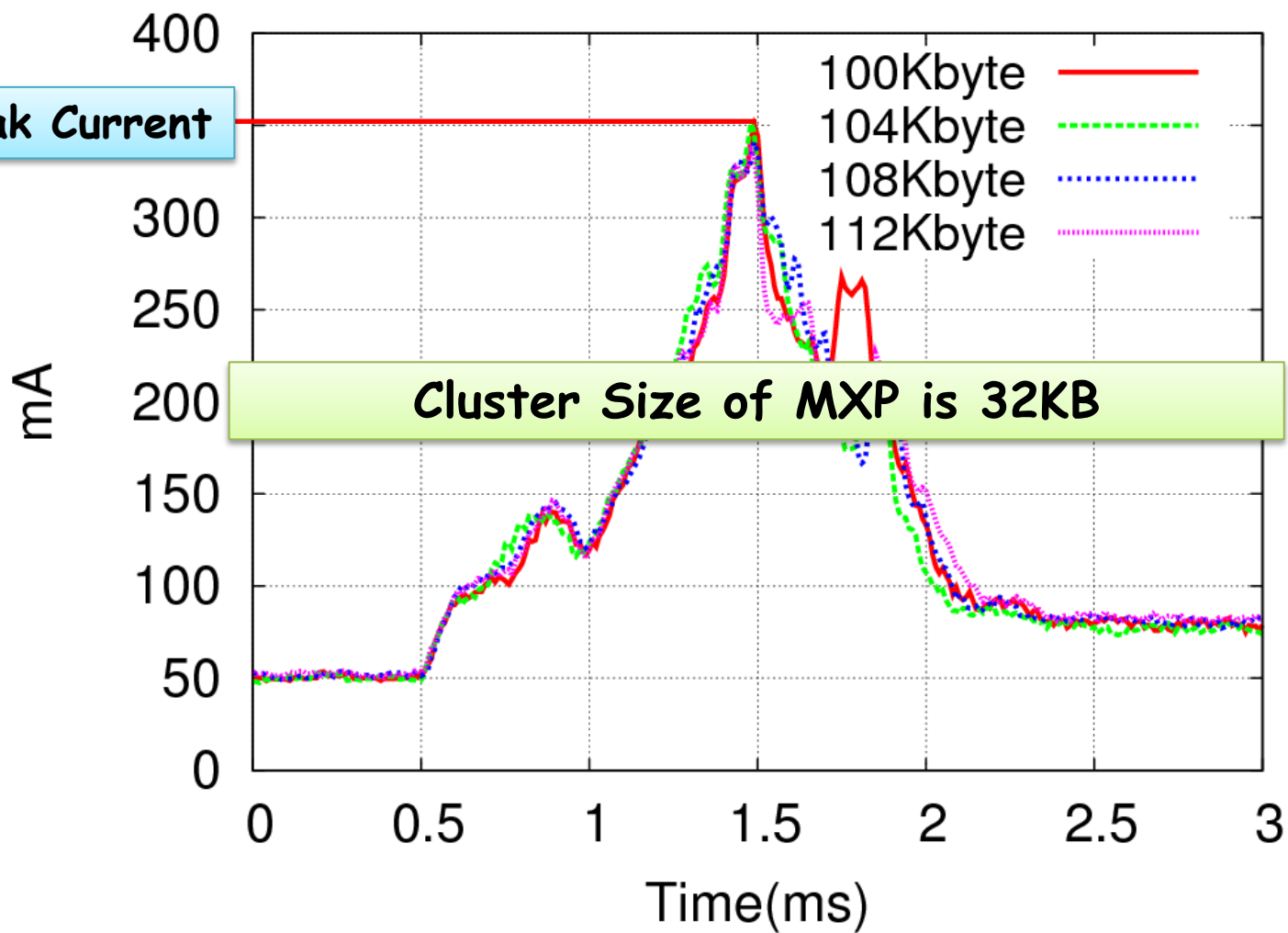
Case Study : SAMSUNG MXP



Case Study : SAMSUNG MXP



Case Study : SAMSUNG MXP

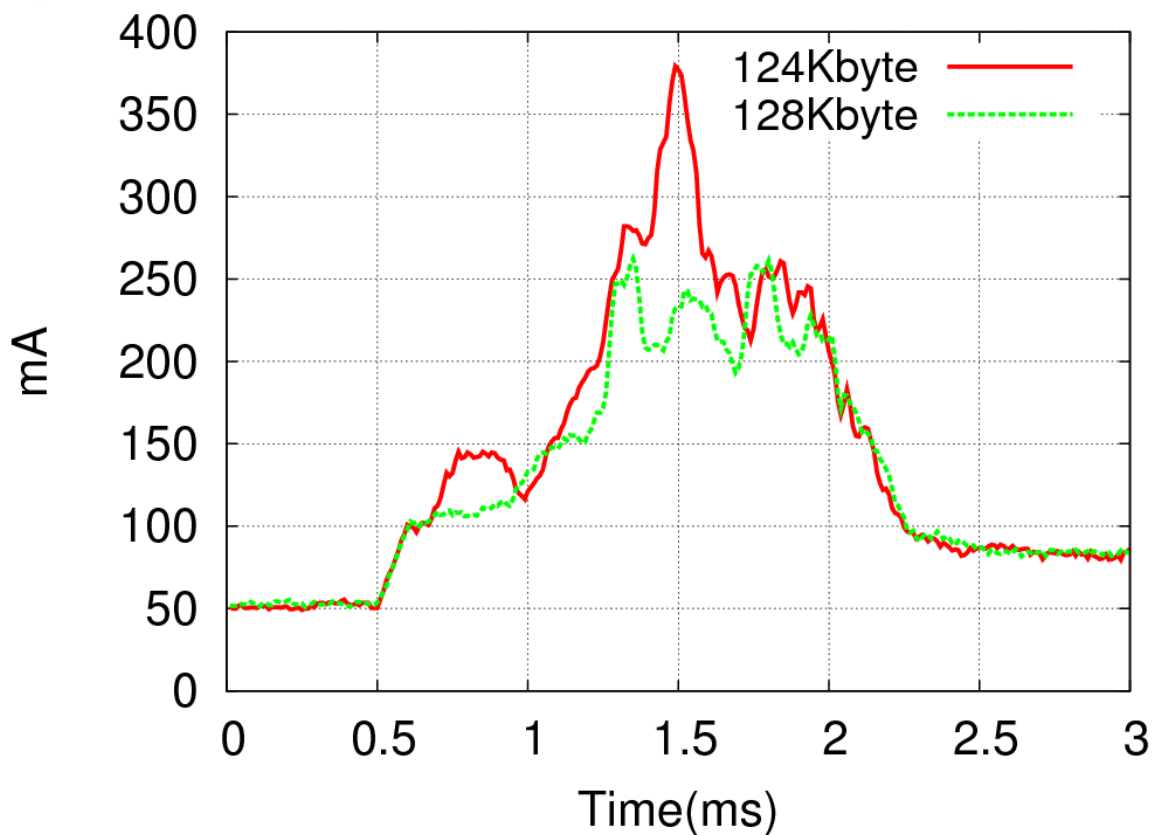


Case Study : SAMSUNG MXP

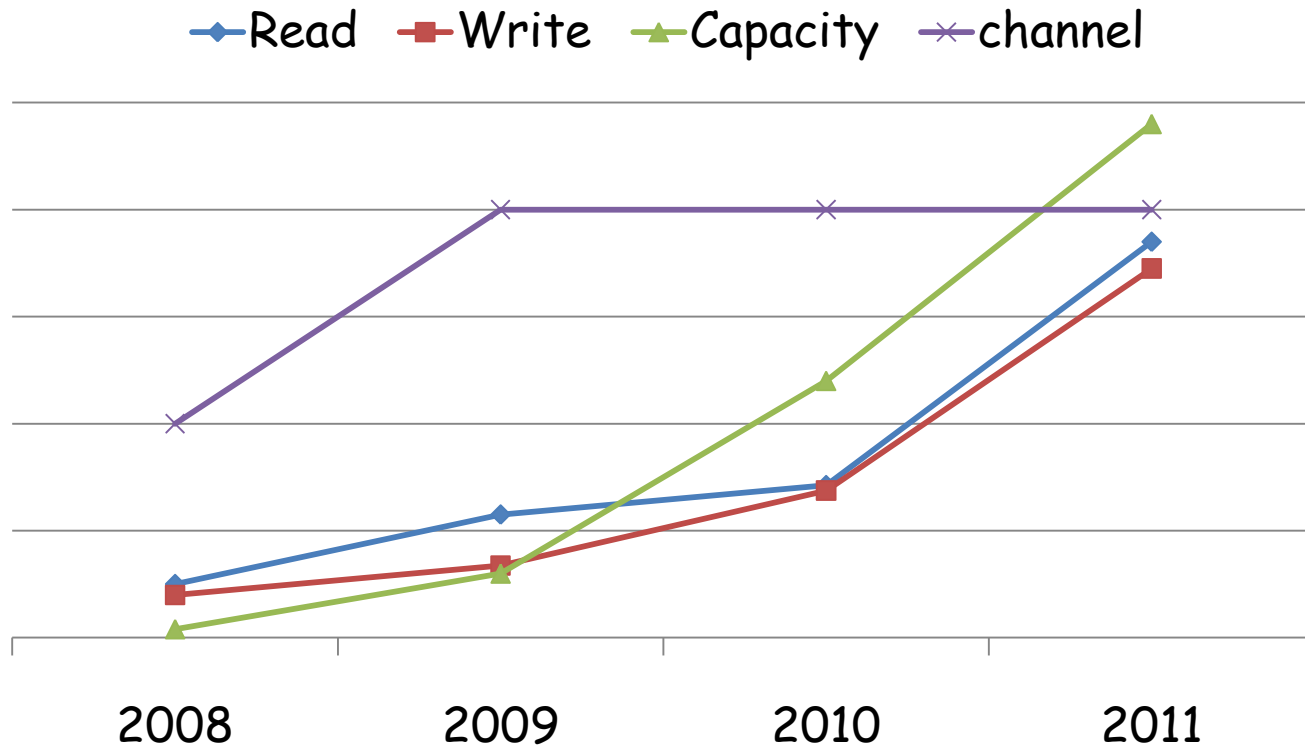


What we still do not know of

Peak of 128 Kbyte < Peak Current of 124 KByte



Forth Coming Problem in Multi-channel SSD

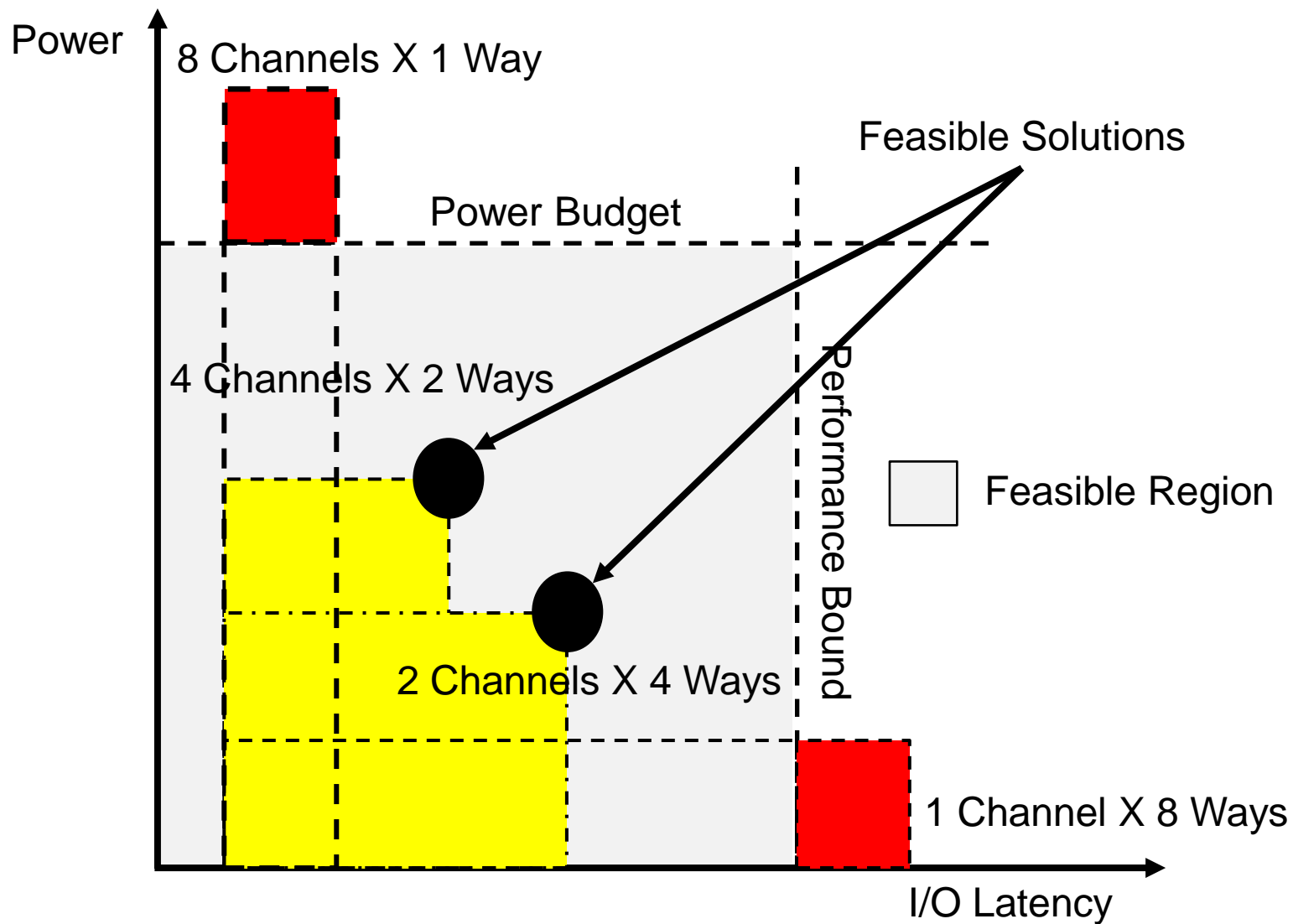


Model Name	Release
SATA3035 (Mtron)	2008.01
Vertex (OCZ)	2009.03
Vertex2 (OCZ)	2010.07
REVO Drive X2 (OCZ)	2011.01

Forth Coming Problem in Multi-channel SSD

- 10 channel: peak 500 mA
- 16 Channel: peak 800 - 900 mA → SSD is no long Green.
- Further, excessive peak current can cause...
 - ✓ supply voltage drop
 - ✓ ground bounce
 - ✓ signal noise
 - ✓ black-out
 - ✓ Etc...

Power Budget



Summary

	X25M	MXP
✓ Cluster Size :	4KB	32KB
✓ programming:	17 mA	35mA
✓ Peak Current :	500mA	350mA
✓ Channel switch:	30 μ sec	
✓ Energy		
✓ Performance		
✓ Small Write		
✓ Large write		
✓ Standby current		

Summary

- Energy Consumption is very good tool to characterize SSD.
- For larger number of channels, peak current will soon be a significant issue.
- We introduce the notion of Power Budget to resolve this issue.

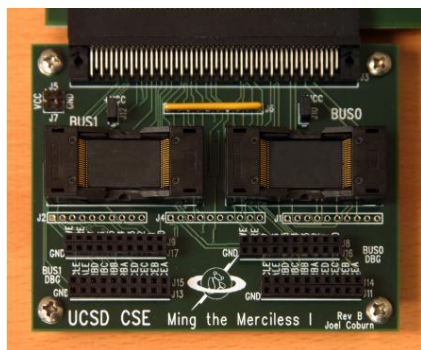


Related Works

- Dongkun Shin et al, NVRAMOS 2010 Spring

Applied different workloads(random, sequential, etc) to SSDs and Measured the power consumption

- Laura M. Grupp et al, MICRO 2009



Custom Board + Flash Memory



Basic Operation



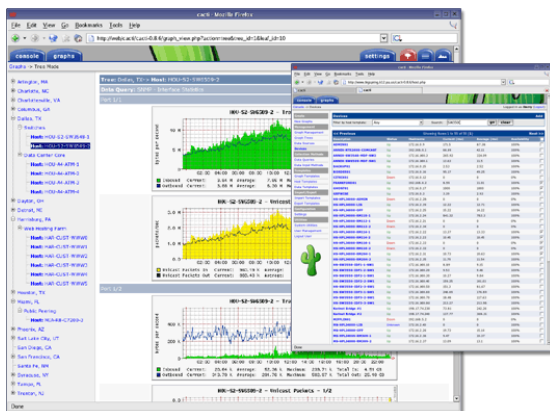
Power Consumption of Flash Memory Basic Operations

Related Works

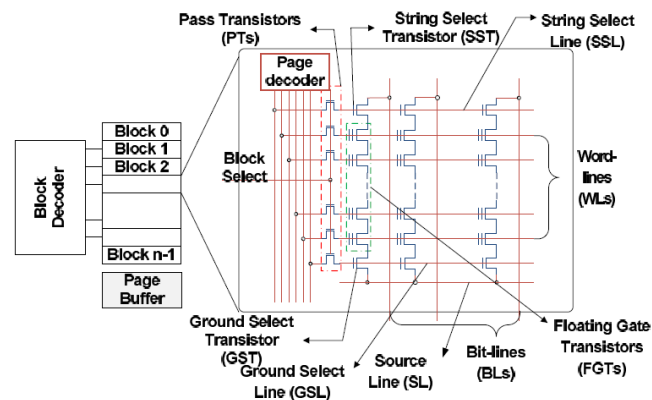
- Euiseong Seo et al, HotPower'08

Applied different workloads (random, sequential, etc) to SSDs with different request sizes (varied the file systems)
Measured the Power Consumption

- Vidyabhushan Mohan et al, Date '10



CACTI 5.3

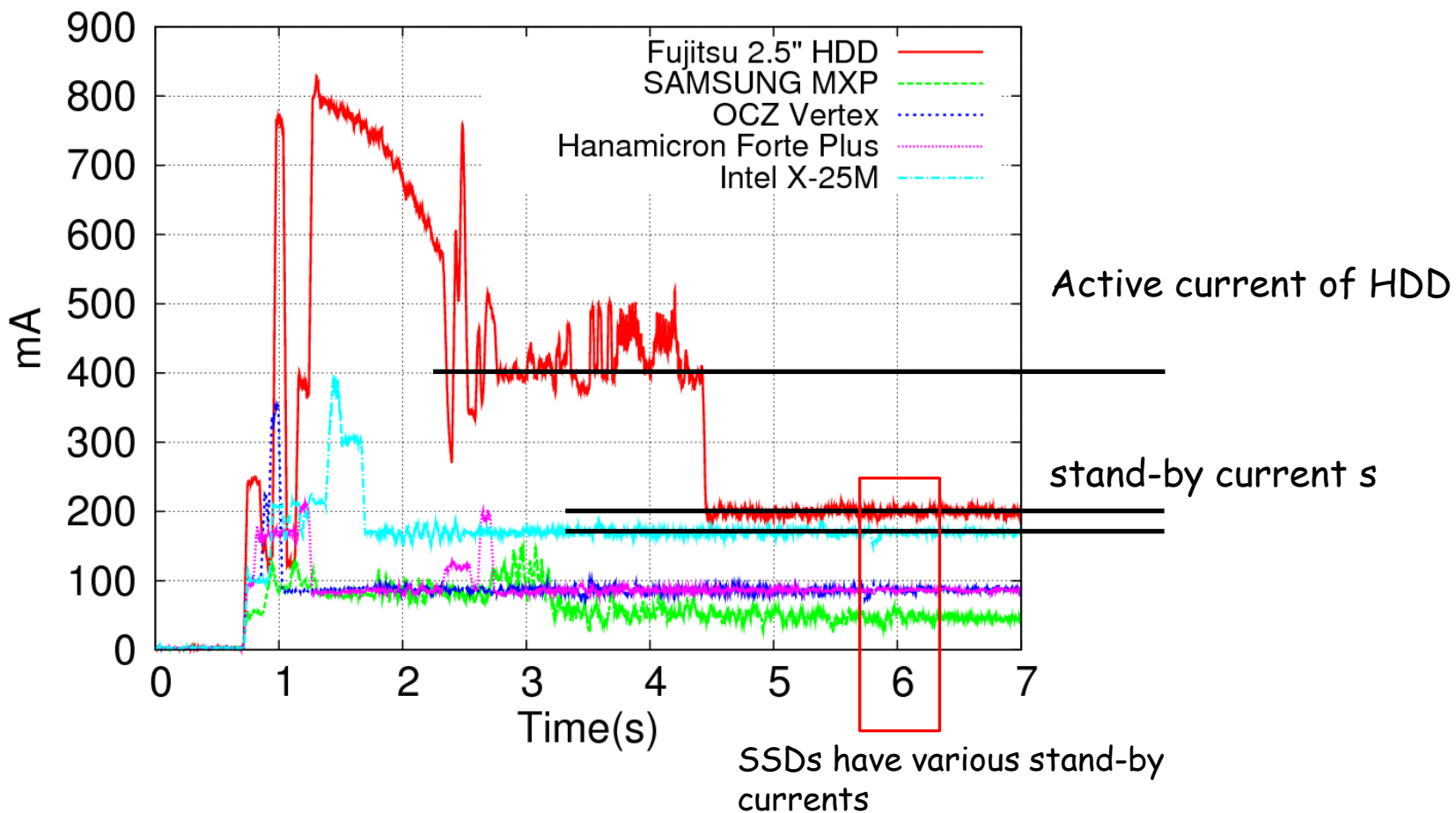


developed a detailed power model for the NAND flash chip itself with CACTI 5.3

Operations on NAND Flash Cell

Model	Read (mA)	Write (mA)	Erase (mA)	Voltage(V)
MD332B (Intel)	20	20	20	3.3
K9XXG08XXM (Samsung)	25	25	25	3.3
MT29FXXG08CXXBB (Micron)	20	20	20	3.3

Power Consumption of Storage Devices: System Boot

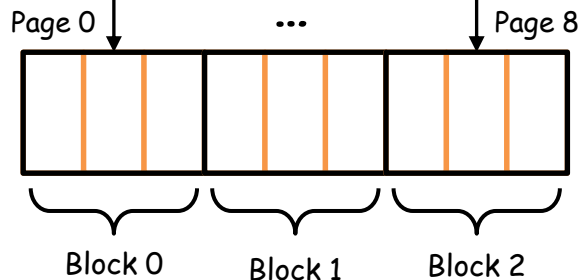


□ FTL

LPN: Logical Page Number

Write to LPN = 3 Write to LPN = 5

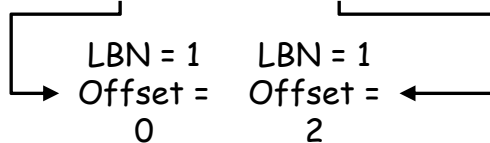
LPN	0	1	2	3	4	5	Mapping Table
PPN	12	11	10	1	3	7	



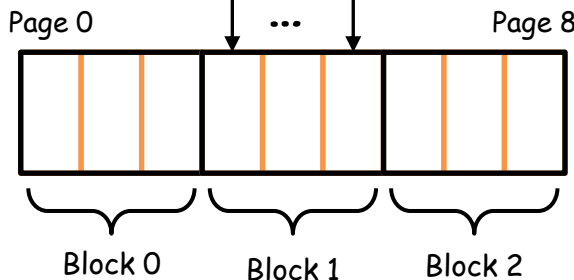
Flash Memory
Page FTL

PPN: Physical Page Number

Write to LPN = 3 Write to LPN = 5



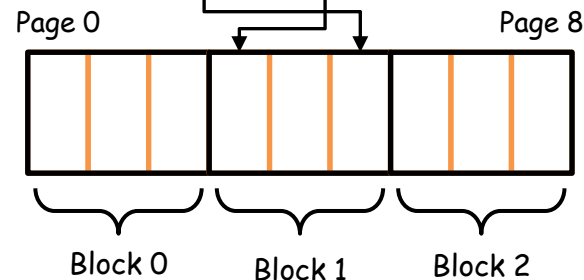
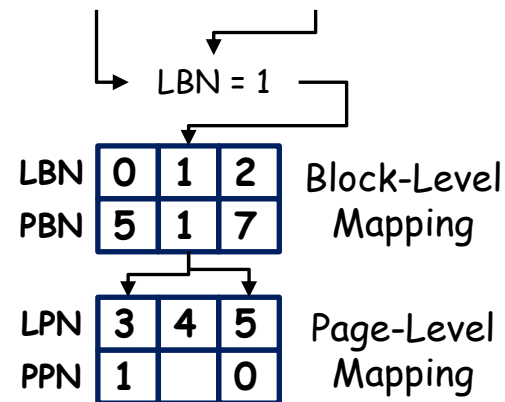
LBN	0	1	2	Mapping Table
PBN	5	1	7	



Flash Memory
Block FTL

PBN: Physical Block Number

Write to LPN = 3 Write to LPN = 5

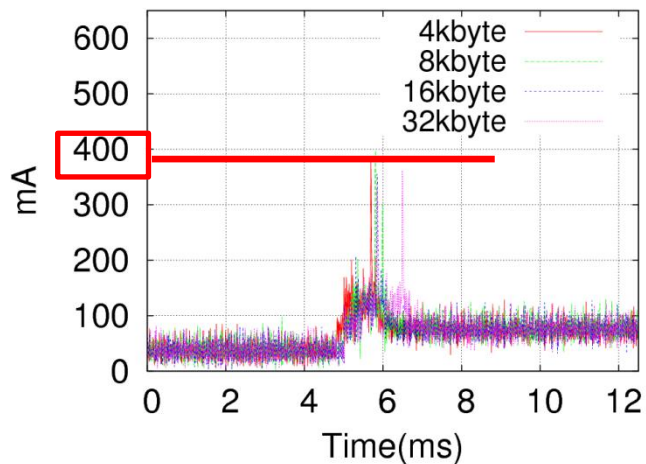


Flash Memory
Hybrid FTL

Trivia in Measurement Methodology

Trivia of Measurement Methodology

- Sampling interval should be small enough.(Read/Program Latency)
- Smoothing the data to filter out measurement noise.



Smoothing

